

Plasma Etching for CMOS Technology and ULSI Applications

Veranstaltung - Plasma Etching for CMOS Technology and ULSI Applications

Titel	Plasma Etching for CMOS Technology and ULSI Applications
Wann	Mi, 26. Oktober 2016 - Fr, 28. Oktober 2016

Beschreibung

Plasma Etching for CMOS Technology and ULSI Applications

TECHNOLOGY FOCUS OF THIS COURSE

Extensive efforts to miniaturize semiconductor devices is largely attributed to lithography and etching technologies that allow semiconductor thin films patterning in the range of dimensions determined by the semiconductor road map. During more than 30 years, classical materials, such as aluminum, SiO₂, and poly-silicon, have been integrated in semiconductor devices.

Nowadays, the technology imposes to work with new materials at each technological node. The integration of new high k and low k dielectric materials, metals at the front and back end of device fabrication, bring on new problem categories. This imposes the necessity to quickly build up expertise at a rate unprecedented in all the history of semiconductor manufacturing.

COURSE CONTENT AND OBJECTIVES

This course is intended to provide an understanding of plasma processes for CMOS applications and ULSI technology. We will discuss fundamental and practical aspects of front end and back end plasma processes for deep submicron CMOS logic processes.

The course is based on experimental results obtained using commercial etchers connected to very powerful diagnostics of the plasma and the plasma surface interaction. The discussions cover several aspects of etch processes of materials integrated in advanced CMOS devices, etch mechanisms, and situations that may be encountered for some important plasma processes.

Please visit following website for more information:

<http://www.cei.se/find-your-course/semiconductor-technology/electronic-and-photonic-devices/c88-plasma-etching-for-cmos-technology-and-ulsi-applications.aspx>

Lokalität - Grenoble

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